Automotive N-Channel 30 V (D-S) 175 °C MOSFET

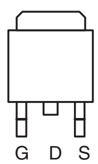
PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0060
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0085
I_D (A)	60
Configuration	Single

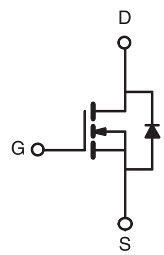
FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified[d]
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

AUTOMOTIVE GRADE
RoHS COMPLIANT
HALOGEN FREE

TO-263





N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM85N03-06P-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C[a]	I_D	60	A
	T_C = 125 °C		55	
Continuous Source Current (Diode Conduction)[a]		I_S	60	
Pulsed Drain Current[b]		I_{DM}	240	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	46	
Single Pulse Avalanche Energy		E_{AS}	105	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	100	W
	T_C = 125 °C		33	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.5	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).
d. Parametric verification ongoing.

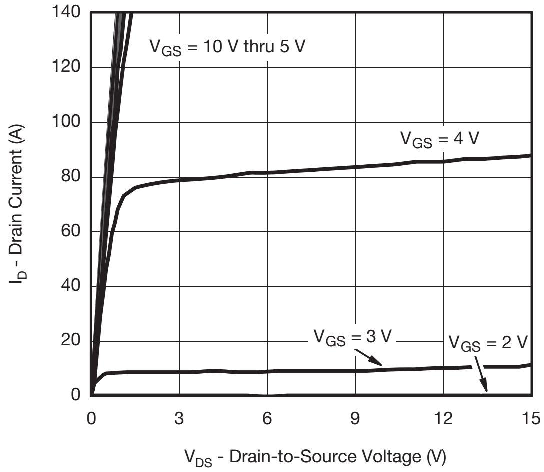
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		30	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA		1.5	2.0	2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 30 V	-	-	1	μA
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 175 °C	-	-	150	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A	-	0.0053	0.0060	Ω
		V_{GS} = 10 V	I_D = 20 A, T_J = 125 °C	-	-	0.0091	
		V_{GS} = 10 V	I_D = 20 A, T_J = 175 °C	-	-	0.0110	
		V_{GS} = 4.5 V	I_D = 20 A	-	0.0072	0.0085	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		-	75	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 15 V, f = 1 MHz	-	3294	4120	pF
Output Capacitance	C_{oss}			-	655	820	
Reverse Transfer Capacitance	C_{rss}			-	351	440	
Total Gate Charge[c]	Q_g	V_{GS} = 10 V	V_{DS} = 15 V, I_D = 50 A	-	47	70	nC
Gate-Source Charge[c]	Q_{gs}			-	7.9	-	
Gate-Drain Charge[c]	Q_{gd}			-	8.2	-	
Gate Resistance	R_g	f = 1 MHz		0.5	1.6	2.8	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.3 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_g = 1 Ω		-	10	15	ns
Rise Time[c]	t_r			-	7	11	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	32	48	
Fall Time[c]	t_f			-	6	9	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}			-	-	240	A
Forward Voltage	V_{SD}	I_F = 30 A, V_{GS} = 0 V		-	0.85	1.5	V

Notes

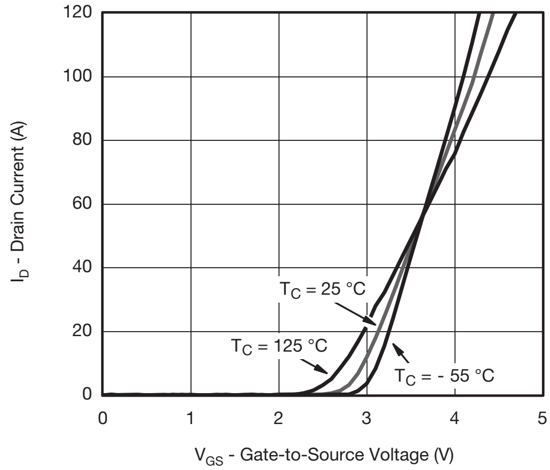
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

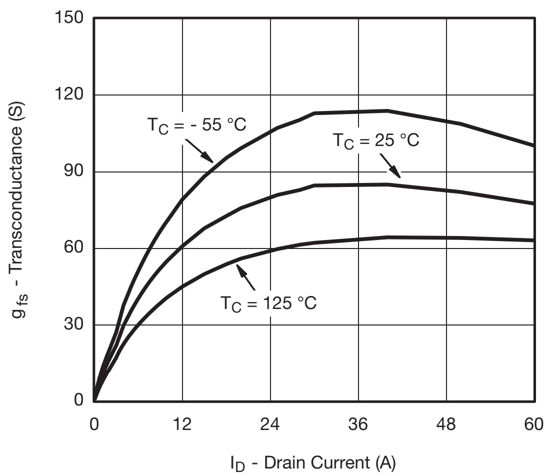
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



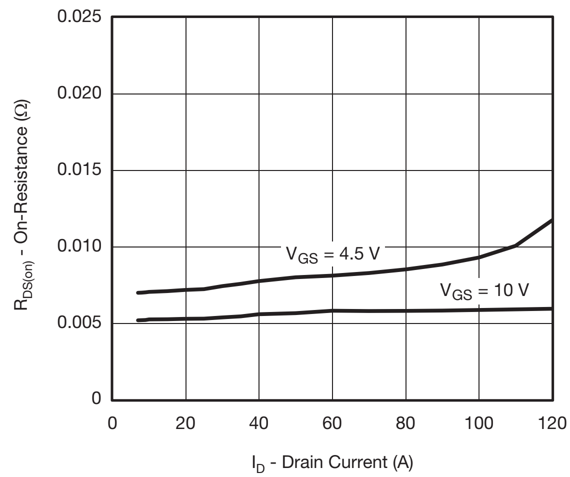
Output Characteristics



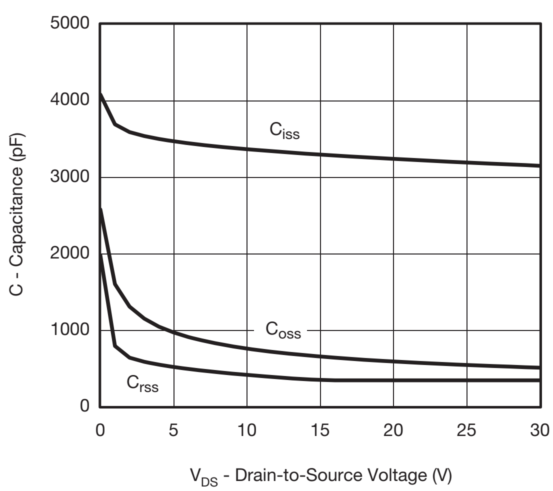
Transfer Characteristics



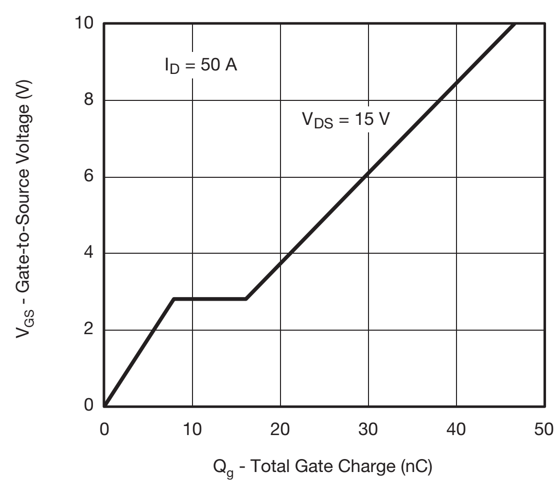
Transconductance



On-Resistance vs. Drain Current

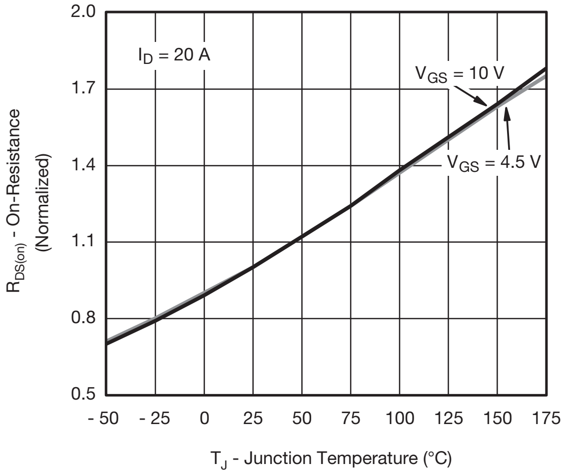


Capacitance

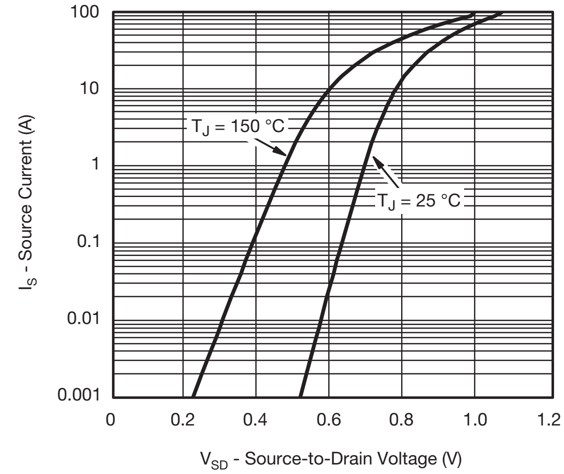


Gate Charge

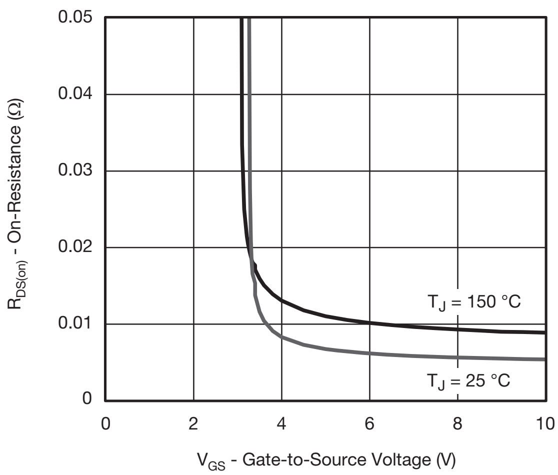
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



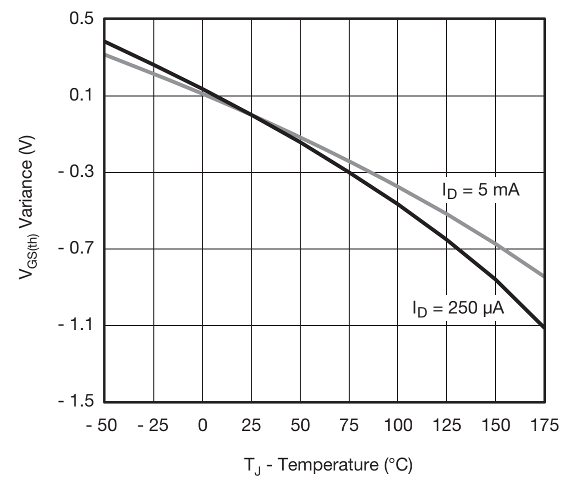
On-Resistance vs. Junction Temperature



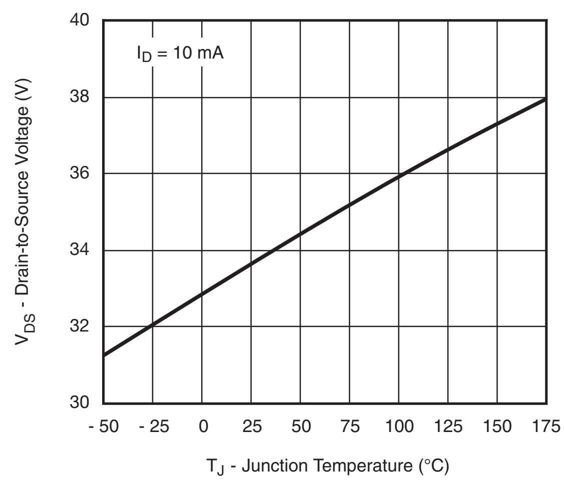
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

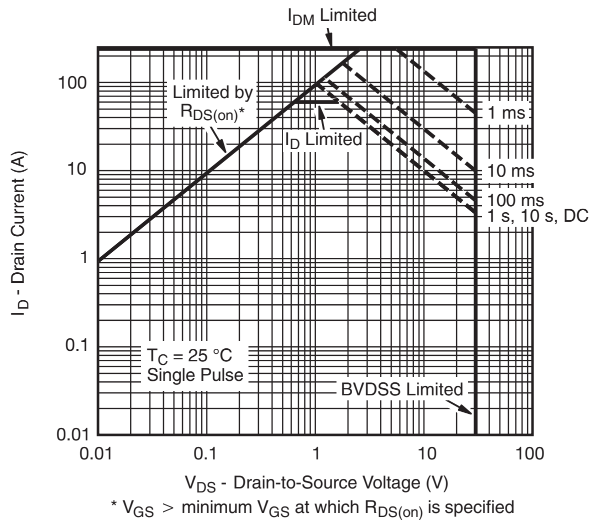


Threshold Voltage

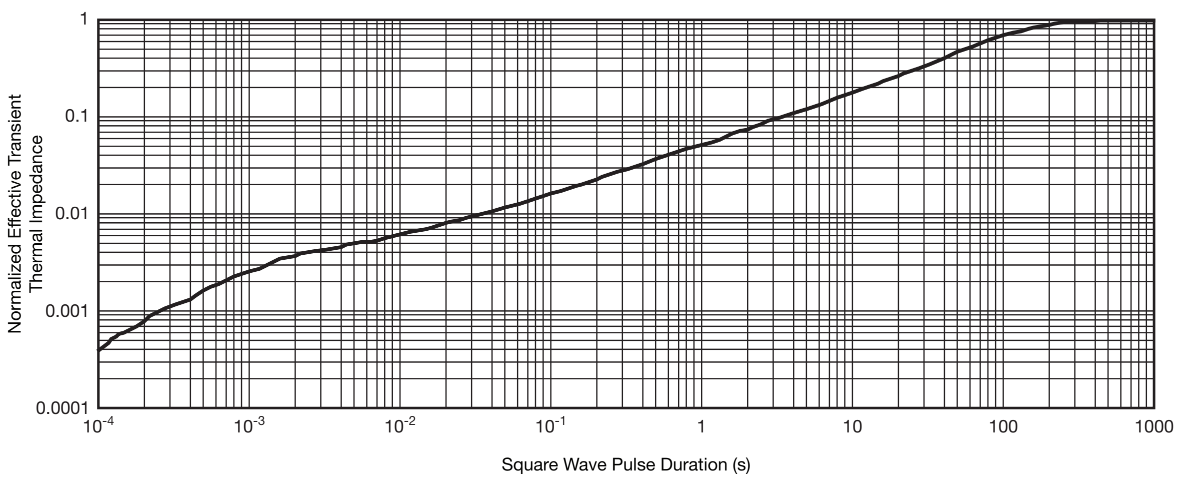


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

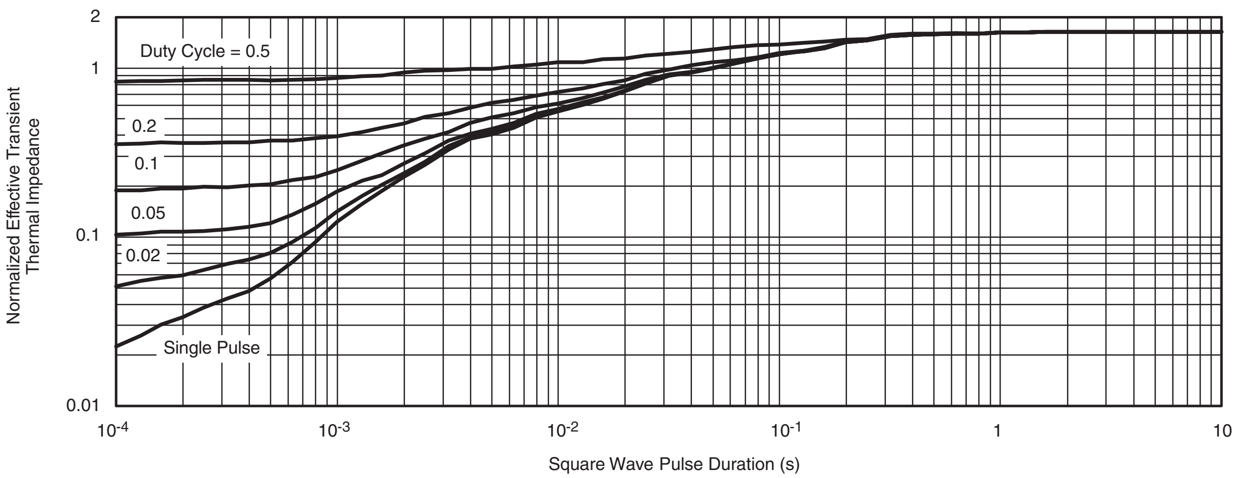


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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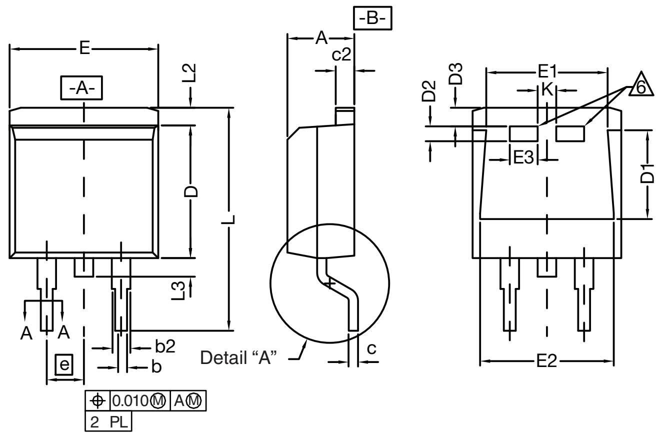
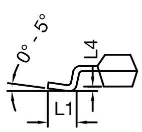
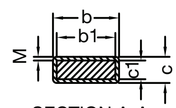
TO-263 (D^{2}PAK): 3-LEAD





DETAIL A (ROTATED 90°)



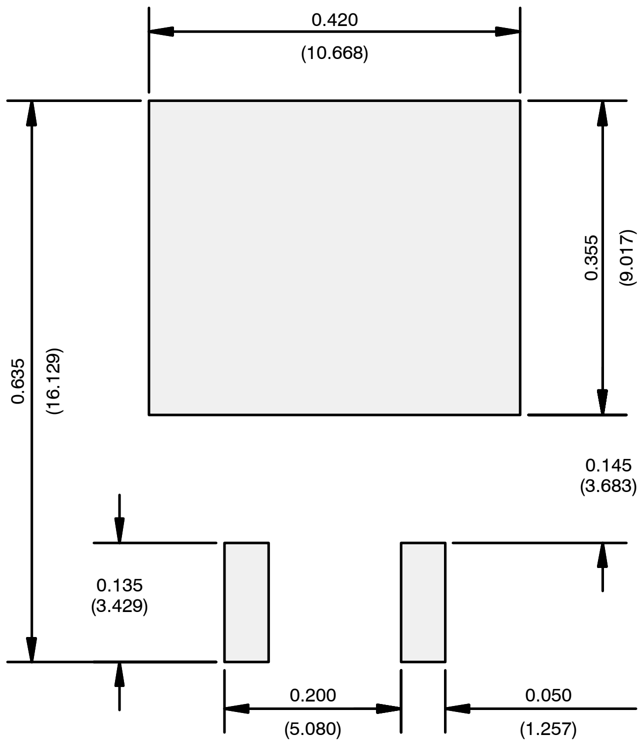
SECTION A-A

DIM.		INCHES MIN.	INCHES MAX.	MILLIMETERS MIN.	MILLIMETERS MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050
ECN: T10-0738-Rev. J, 03-Jan-11 DWG: 5843					

Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. *: Thin lead is for SUB, SYB.
   Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D^2PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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